

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- Soft Punch Through Silicon
- Isolated AISiC Base with AlN Substrates
- Lead Free Construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Auxiliaries

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM100PHM33-F000 is a half bridge 3300V soft punch through, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) chopper module configured with the lower arm of the bridge controlled. The IGBT has a wide reverse bias safe operating area (RBSOA). This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM100PHM33-F000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	3300V
$V_{CE(sat)}$ * (typ)	2.8V
I_C (max)	100A
$I_{C(PK)}$ (max)	200A

* Measured at the auxiliary terminals

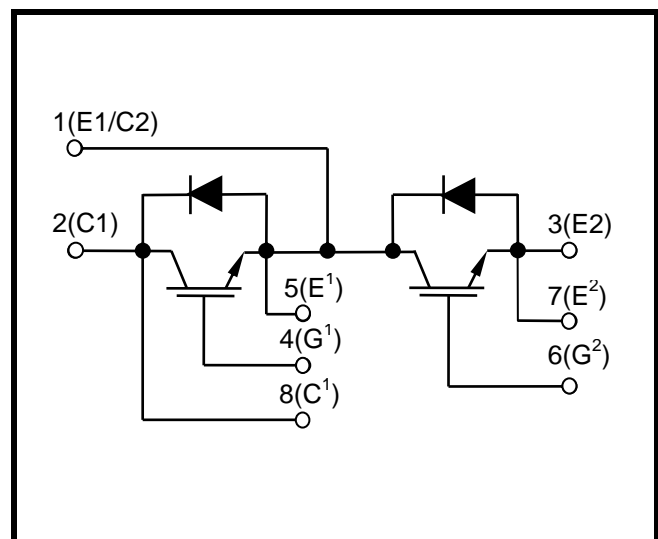
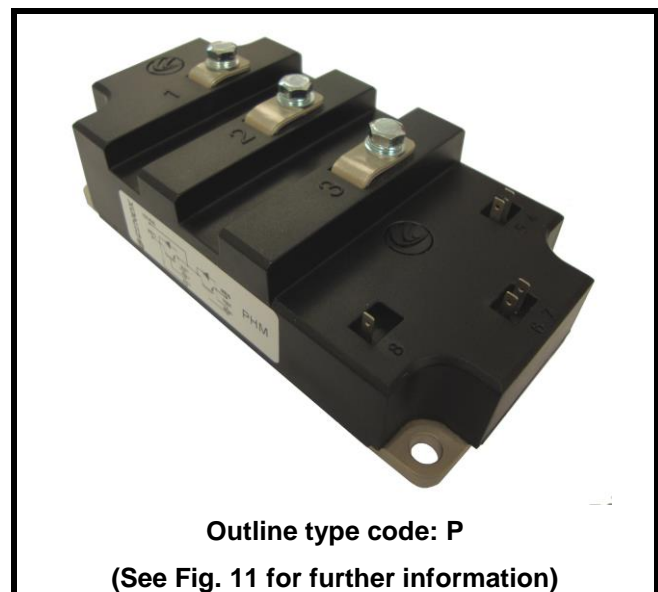


Fig. 1 Circuit configuration



Outline type code: P

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under ‘Absolute Maximum Ratings’ may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V _{CES}	Collector-emitter voltage	V _{GE} = 0V	3300	V
V _{GES}	Gate-emitter voltage		±20	V
I _C	Continuous collector current	T _{case} = 90°C	100	A
I _{C(PK)}	Peak collector current	1ms, T _{case} = 115°C	200	A
P _{max}	Max. transistor power dissipation	T _{case} = 25°C, T _j = 150°C	1.3	kW
I ² t	Diode I ² t value	V _R = 0, t _p = 10ms, T _j = 125°C	5	kA ² s
V _{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q _{PD}	Partial discharge – per module	IEC1287, V ₁ = 3500V, V ₂ = 2600V, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AIN
 Baseplate material: AISiC
 Creepage distance: 33mm
 Clearance: 20mm
 CTI (Comparative Tracking Index): >600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
R _{th(j-c)}	Thermal resistance – transistor	Continuous dissipation - junction to case	-	-	96	°C/kW
R _{th(j-c)}	Thermal resistance – Diode	Continuous dissipation - junction to case	-	-	192	°C/kW
R _{th(c-h)}	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	16	°C/kW
T _j	Junction temperature	Transistor	-	-	150	°C
		Diode	-	-	125	°C
T _{stg}	Storage temperature range	-	-40	-	125	°C
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M5	-	-	4	Nm

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 125^{\circ}C$			8	mA
I_{GES}	Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$		400		nA
$V_{GE(TH)}$	Gate threshold voltage	$I_C = 10mA, V_{GE} = V_{CE}$	5.5	6.5	7.0	V
$V_{CE(sat)}^{\dagger}$	Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 100A$		2.8		V
		$V_{GE} = 15V, I_C = 100A, T_j = 125^{\circ}C$		3.6		V
I_F	Diode forward current	DC		100		A
I_{FM}	Diode maximum forward current	$t_p = 1ms$		200		A
V_F^{\dagger}	Diode forward voltage	$I_F = 100A$		2.9		V
		$I_F = 100A, T_j = 125^{\circ}C$		3.0		V
C_{ies}	Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		18		nF
Q_g	Gate charge	$\pm 15V$		2.5		μC
C_{res}	Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		0.28		nF
L_M	Module inductance			40		nH
R_{INT}	Internal transistor resistance			540		$\mu\Omega$
SC_{Data}	Short circuit current, I_{SC}	$T_j = 125^{\circ}C, V_{CC} = 2500V$ $t_p \leq 10\mu s, V_{GE} \leq 15V$ $V_{CE(max)} = V_{CES} - L^* \times dl/dt$ IEC 60747-9		470		A

Note:

\dagger Measured at the the auxiliary terminals

* L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions		Min	Typ.	Max	Units
t _{d(off)}	Turn-off delay time	I _C = 100A V _{GE} = ±15V V _{CE} = 1800V C _{ge} = 33nF L _S ~ 100nH	R _{G(ON)} = 33Ω R _{G(OFF)} = 33Ω		1950		ns
t _f	Fall time				170		ns
E _{OFF}	Turn-off energy loss				110		mJ
t _{d(on)}	Turn-on delay time				1180		ns
t _r	Rise time				225		ns
E _{ON}	Turn-on energy loss		R _{G(ON)} = 16.5Ω, R _{G(OFF)} = 33Ω	150		mJ	
Q _{rr}	Diode reverse recovery charge	I _F = 100A V _{CE} = 1800V di _F /dt = 800A/μs		40		μC	
I _{rr}	Diode reverse recovery current			75		A	
E _{rec}	Diode reverse recovery energy			40		mJ	

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions		Min	Typ.	Max	Units
t _{d(off)}	Turn-off delay time	I _C = 100A V _{GE} = ±15V V _{CE} = 1800V C _{ge} = 33nF L _S ~ 100nH	R _{G(ON)} = 33Ω R _{G(OFF)} = 33Ω		2200		ns
t _f	Fall time				190		ns
E _{OFF}	Turn-off energy loss				135		mJ
t _{d(on)}	Turn-on delay time				1150		ns
t _r	Rise time				280		ns
E _{ON}	Turn-on energy loss		R _{G(ON)} = 16.5Ω, R _{G(OFF)} = 33Ω	200		mJ	
Q _{rr}	Diode reverse recovery charge	I _F = 100A V _{CE} = 1800V di _F /dt = 800A/μs		65		μC	
I _{rr}	Diode reverse recovery current			85		A	
E _{rec}	Diode reverse recovery energy			65		mJ	

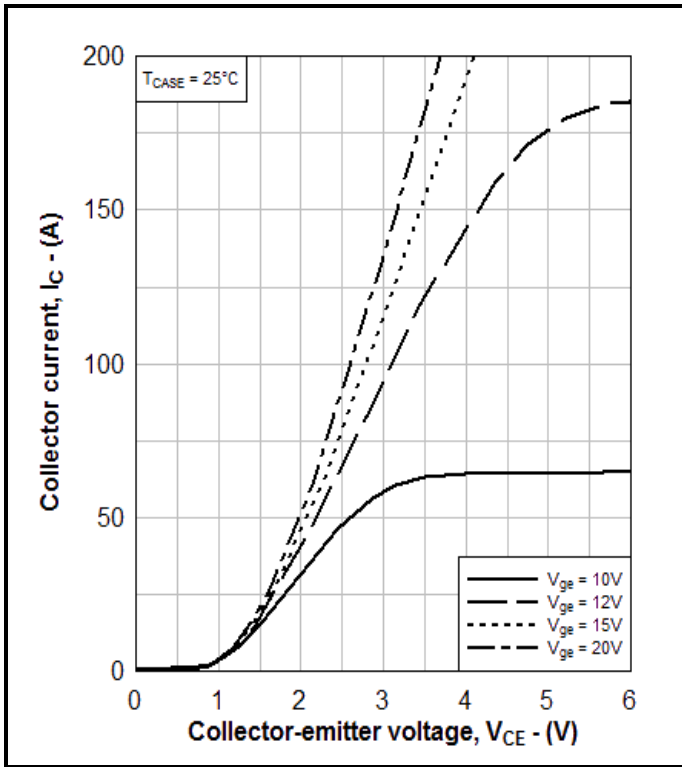


Fig. 3 Typical output characteristics

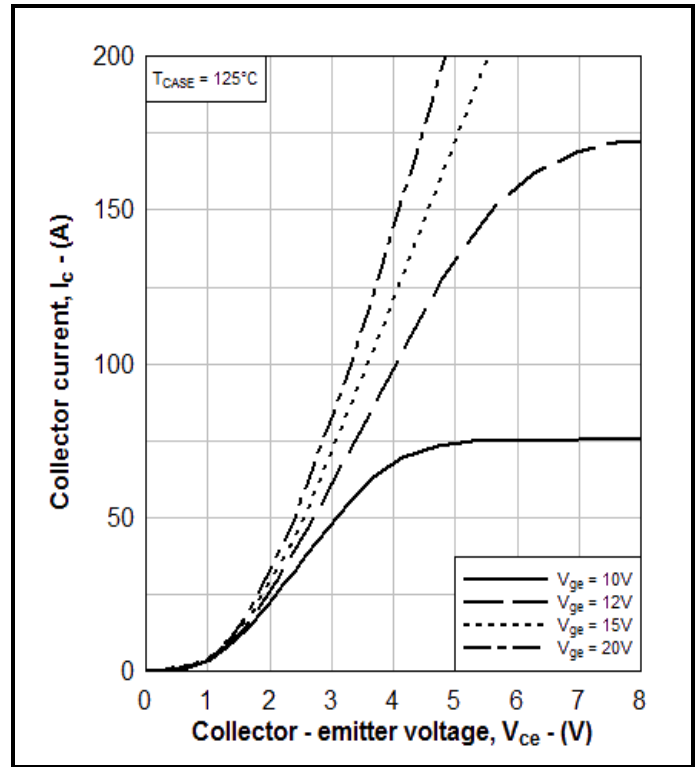


Fig. 4 Typical output characteristics

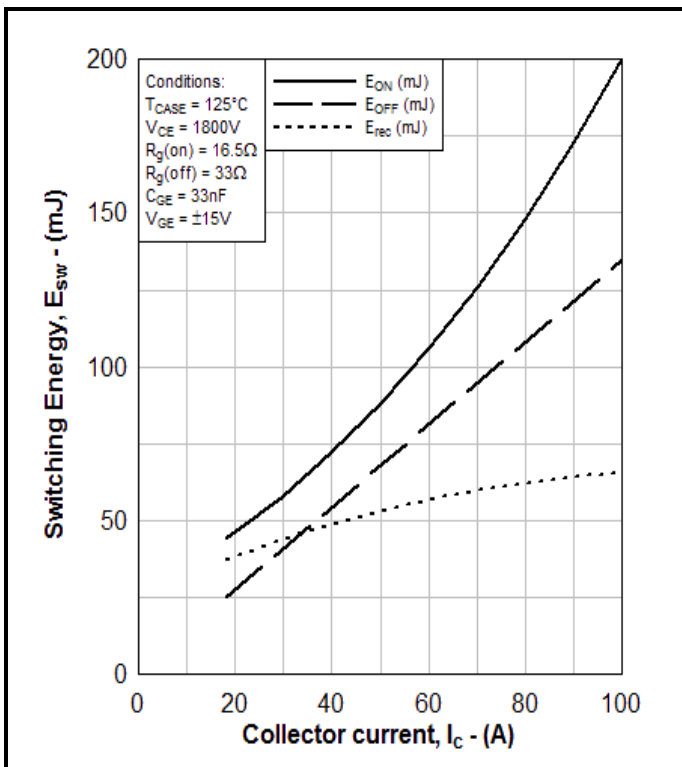


Fig. 5 Typical switching energy vs collector current

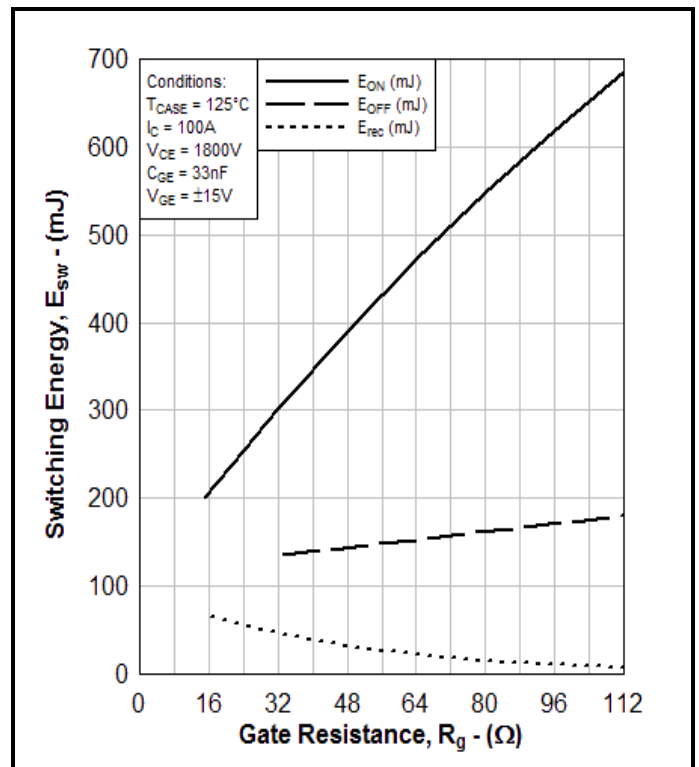


Fig. 6 Typical switching energy vs gate resistance

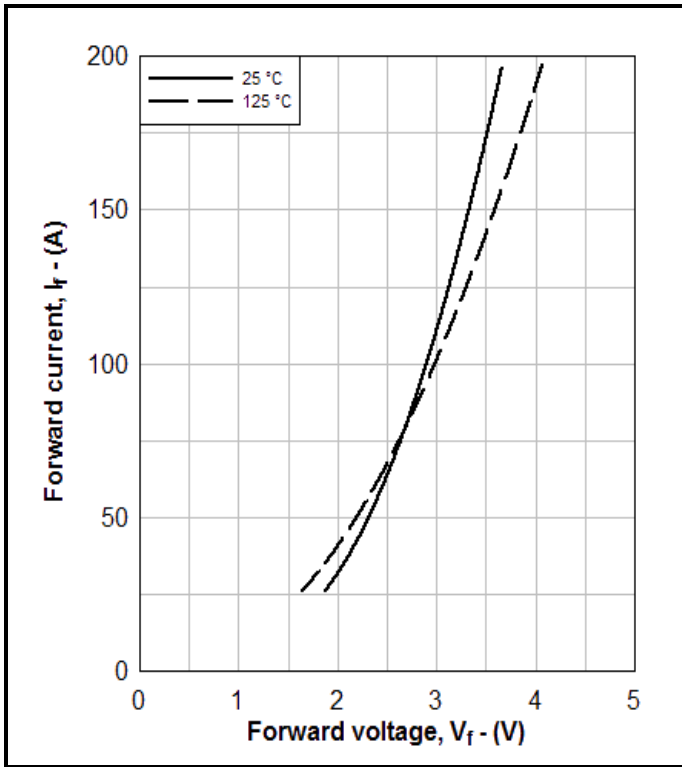


Fig. 7 Diode typical forward characteristics

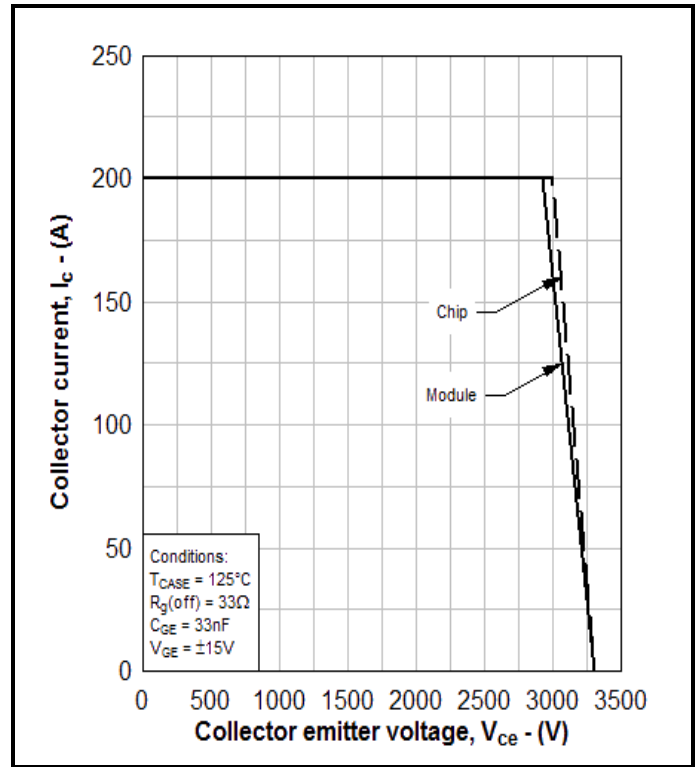


Fig. 8 Reverse bias safe operating area

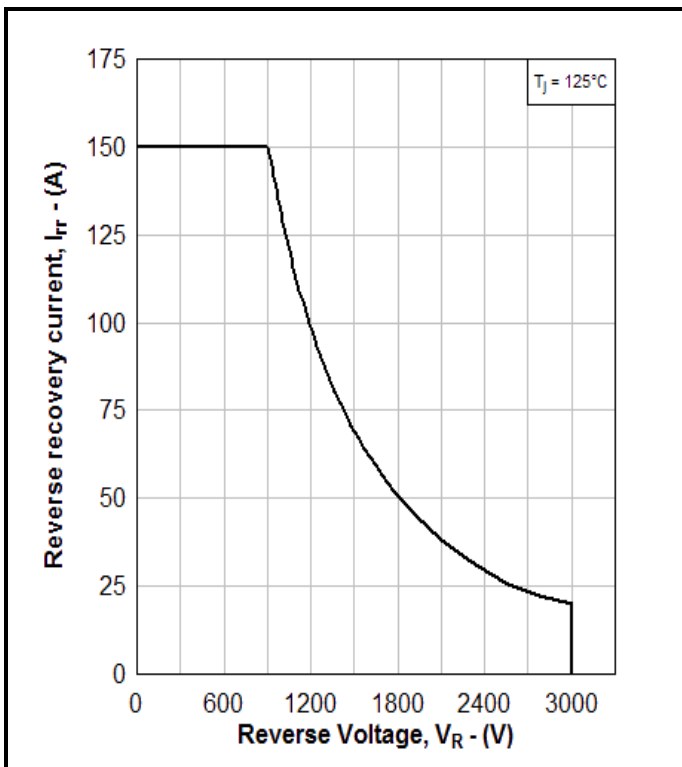


Fig. 9 Diode reverse bias safe operating area

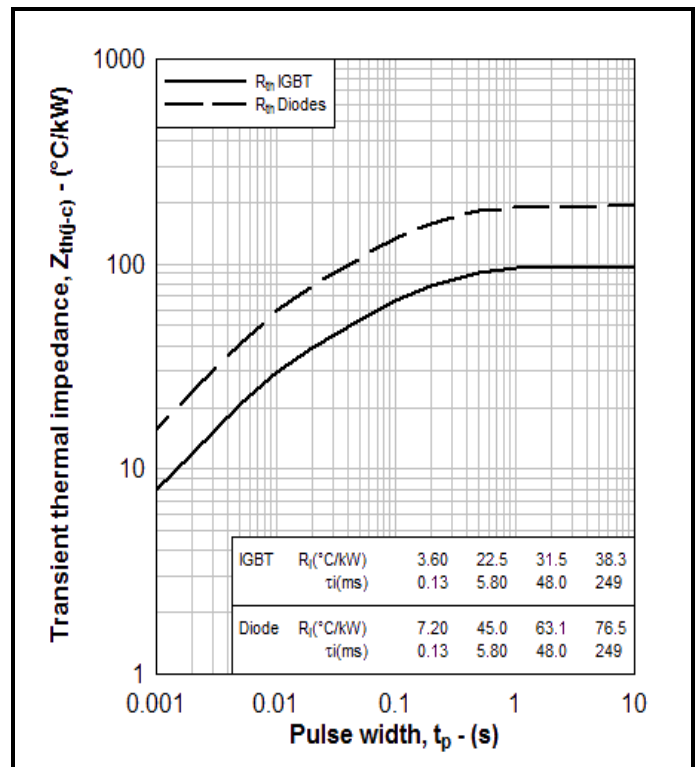
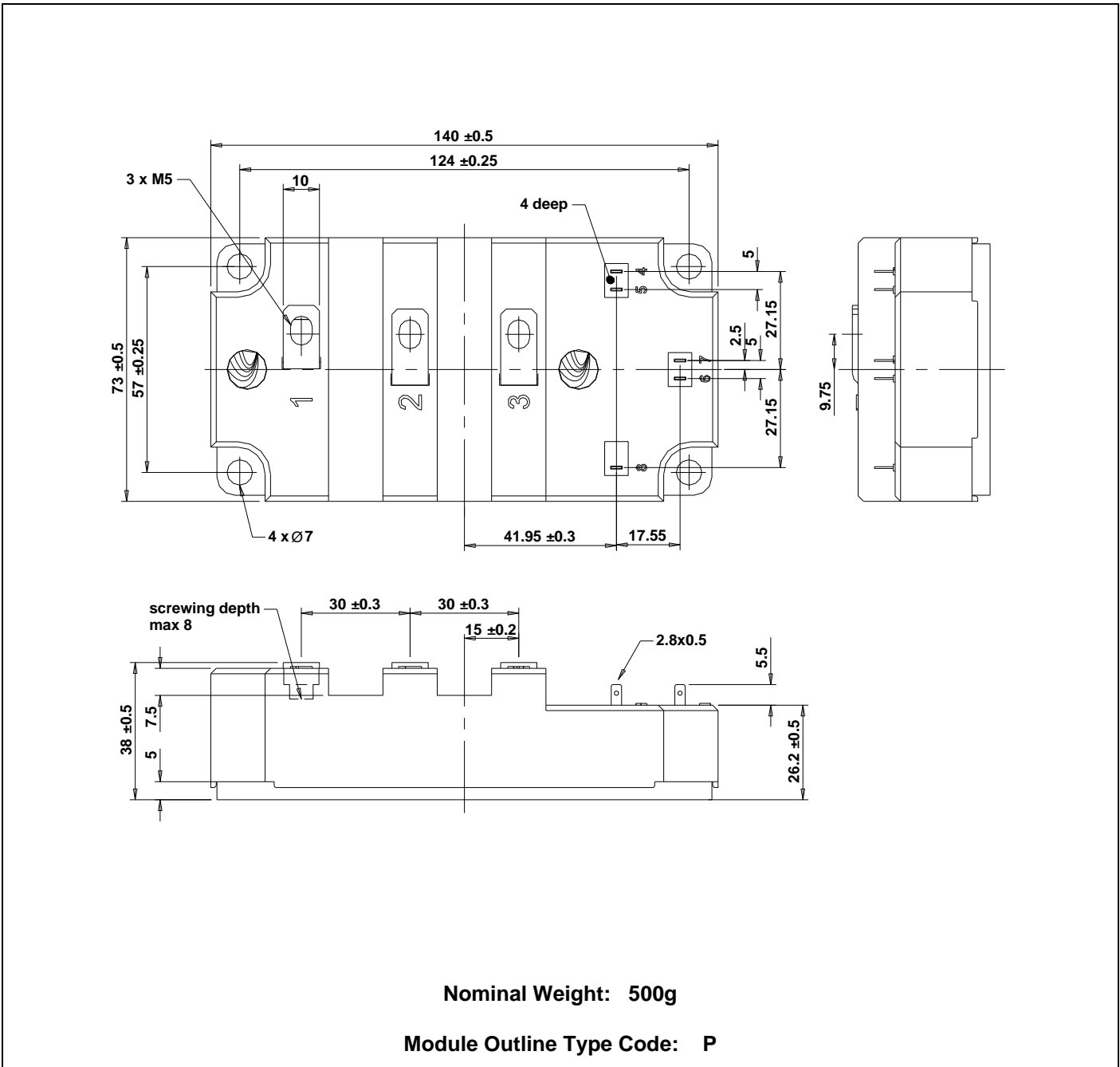


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal Weight: 500g

Module Outline Type Code: P

Fig. 11 Module outline drawing

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HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LTD

Doddington Road, Lincoln, Lincolnshire, LN6 3LF,
United Kingdom

Fax: +44(0)1522 500550

Tel: +44(0)1522 500500

Web: <http://www.dynexsemi.com>

CUSTOMER SERVICE

DYNEX SEMICONDUCTOR LTD

Doddington Road, Lincoln, Lincolnshire, LN6 3LF,
United Kingdom

Tel: +44(0)1522 502753 / 502901

Email: powersolutions@dynexsemi.com